

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _A = +25°C
50V	3.5Ω @ V _{GS} = 10V	0.31A

Description and Applications

This MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) yet maintain superior switching performance, making it ideal for high-efficiency power-management applications.

- Load switches

Features and Benefits

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- ESD Protected Gate**
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- Halogen and Antimony Free. "Green" Device (Note 3)**
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/104/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please [contact us](https://www.diodes.com/quality/product-definitions/) or your local Diodes representative.

<https://www.diodes.com/quality/product-definitions/>

Mechanical Data

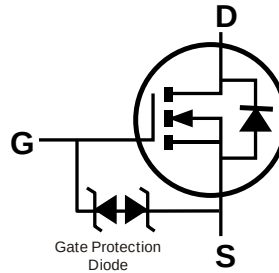
- Package: SOT23
- Package Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish – Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (e3)
- Terminals Connections: See Diagram Below
- Weight: 0.009 grams (Approximate)



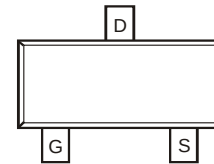
ESD Protected Gate



Top View



Internal Schematic



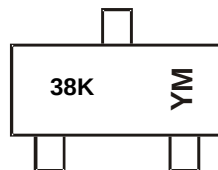
Top View

Ordering Information (Note 4)

Orderable Part Number	Package	Packing	
		Qty.	Carrier
BSS138K-7	SOT23	3,000	Tape & Reel
BSS138K-13	SOT23	10,000	Tape & Reel

- Notes:
- No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
 - See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 - Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 - For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

Marking Information



38K = Product Type Marking Code
YM = Date Code Marking
Y or Y or Y = Year (ex: M = 2025)
M = Month (ex: 9 = September)

Date Code Key

Year	2017	-	2025	2026	2027	2028	2029	2030	2031	2032	2033	2034
Code	E	-	M	N	P	R	S	T	U	V	W	X

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V _{DSS}	50	V
Gate-Source Voltage			V _{GSS}	±20	V
Continuous Drain Current (Note 6) V _{GS} = 10V	Steady State	T _A = +25°C T _A = +70°C	I _D	0.31 0.25	A
Maximum Continuous Body Diode Forward Current (Note 6)			I _S	0.5	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I _{DM}	0.8	A

Thermal Characteristics

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)		P _D	0.38	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	R _{θJA}	338	°C/W
Total Power Dissipation (Note 6)		P _D	0.54	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	R _{θJA}	237	°C/W
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV _{DSS}	50	—	—	V	V _{GS} = 0V, I _D = 250µA
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}	—	—	1	µA	V _{DS} = 50V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±10	µA	V _{GS} = ±20V, V _{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(TH)}	0.5	1.1	1.5	V	V _{DS} = V _{GS} , I _D = 250µA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	1.3	3.5	Ω	V _{GS} = 10V, I _D = 0.22A
Diode Forward Voltage	V _{SD}	—	0.8	1.2	V	V _{GS} = 0V, I _D = 0.22A
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C _{iss}	—	23.2	—	pF	V _{DS} = 25V, V _{GS} = 0V f = 1.0MHz
Output Capacitance	C _{oss}	—	3.1	—	pF	
Reverse Transfer Capacitance	C _{rss}	—	2.2	—	pF	
Gate Resistance	R _g	—	69	—	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1MHz
Total Gate Charge (V _{GS} = 4.5V)	Q _g	—	0.45	—	nC	V _{DS} = 25V, I _D = 0.2A
Total Gate Charge (V _{GS} = 10V)	Q _g	—	0.95	—	nC	
Gate-Source Charge	Q _{gs}	—	0.10	—	nC	
Gate-Drain Charge	Q _{gd}	—	0.14	—	nC	
Turn-On Delay Time	t _{D(ON)}	—	3.2	—	ns	V _{DS} = 25V, V _{GS} = 10V, R _G = 50Ω, I _D = 0.2A
Turn-On Rise Time	t _R	—	2.5	—	ns	
Turn-Off Delay Time	t _{D(OFF)}	—	13.8	—	ns	
Turn-Off Fall Time	t _F	—	7.6	—	ns	
Reverse Recovery Time	t _{RR}	—	8.8	—	ns	I _F = 0.2A, di/dt = 100A/µs
Reverse Recovery Charge	Q _{RR}	—	2.6	—	nC	I _F = 0.2A, di/dt = 100A/µs

- Notes:
- Device mounted on FR-4 PCB, with minimum recommended pad layout.
 - Device mounted on 1" x 1" FR-4 PCB with high coverage 2oz. Copper, single sided.
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to product testing.

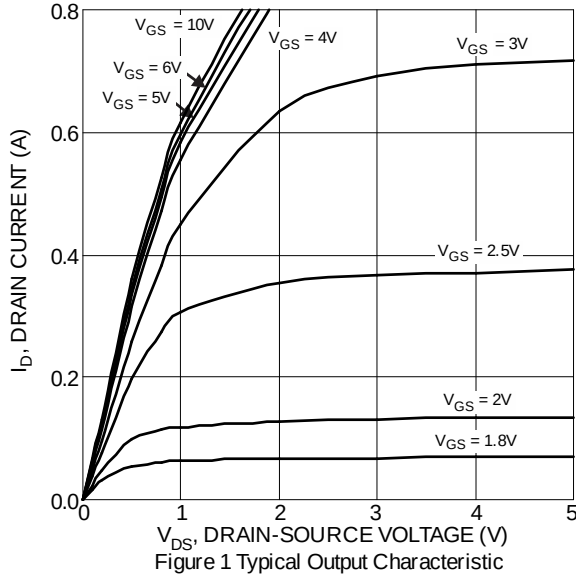


Figure 1 Typical Output Characteristic

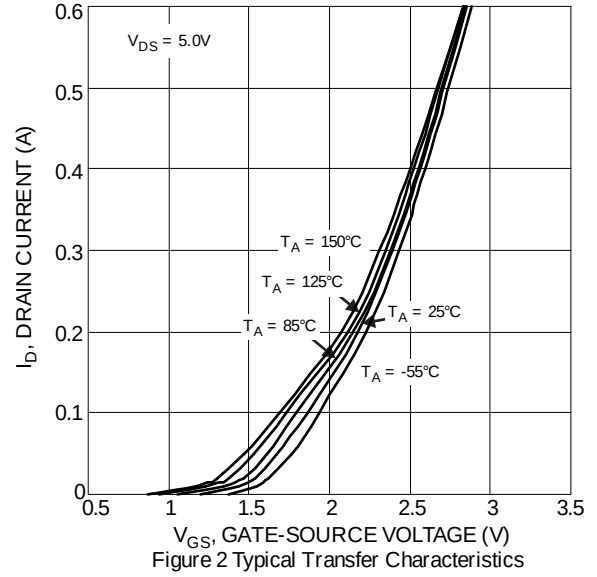


Figure 2 Typical Transfer Characteristics

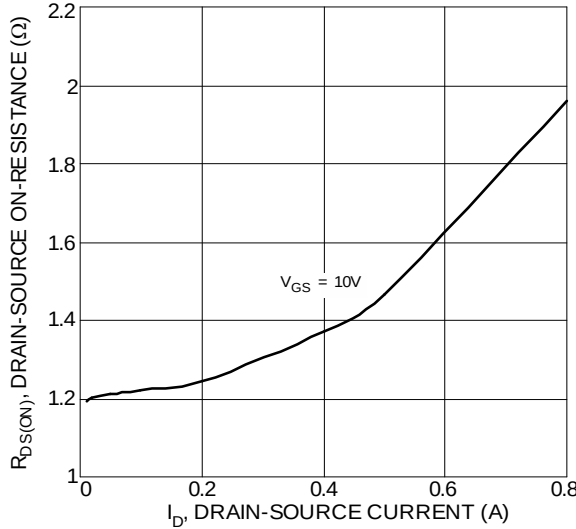


Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage

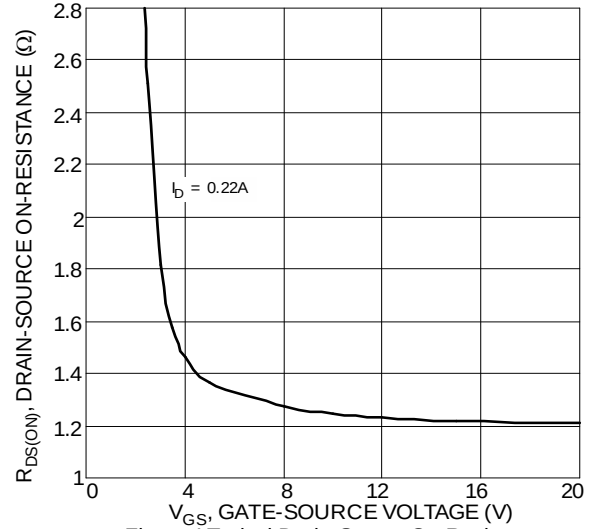


Figure 4 Typical Drain-Source On-Resistance vs. Gate-Source Voltage

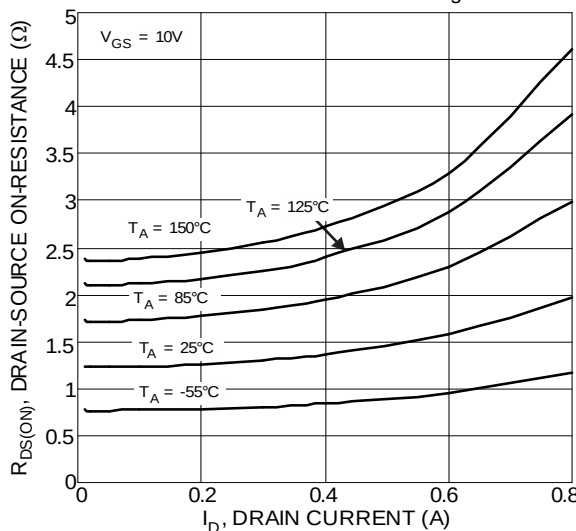


Figure 5 Typical On-Resistance vs. Drain Current and Temperature

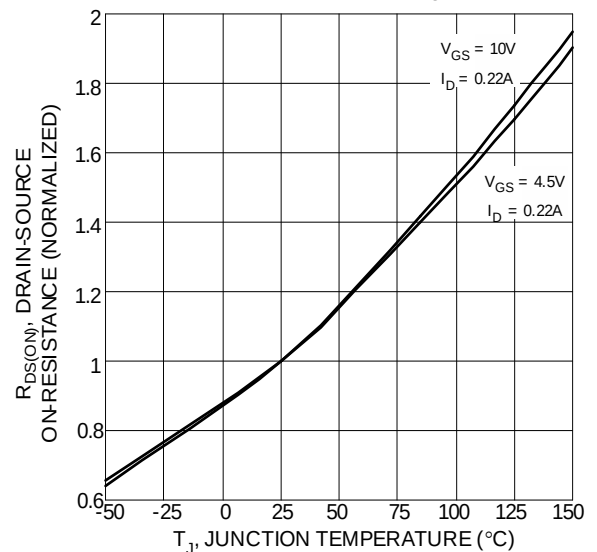


Figure 6 On-Resistance Variation with Temperature

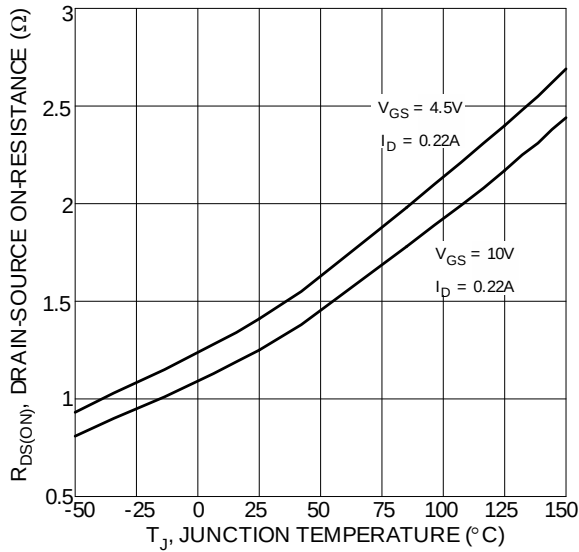


Figure 7 On-Resistance Variation with Temperature

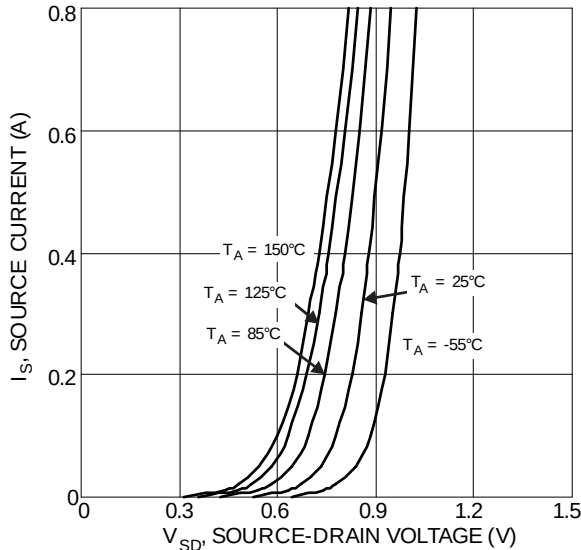


Figure 9 Diode Forward Voltage vs. Current

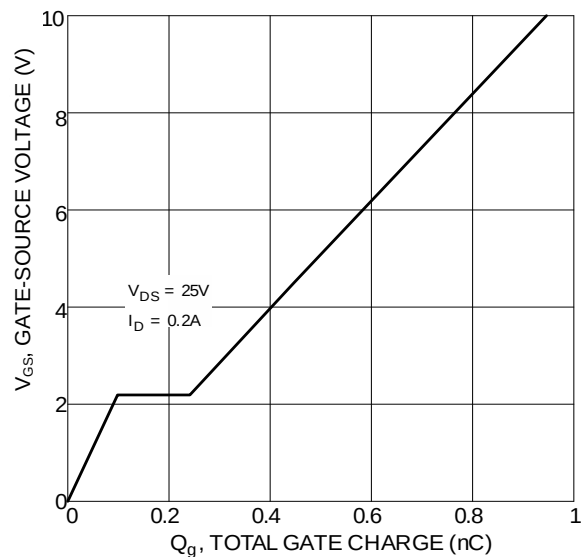


Figure 11 Gate Charge

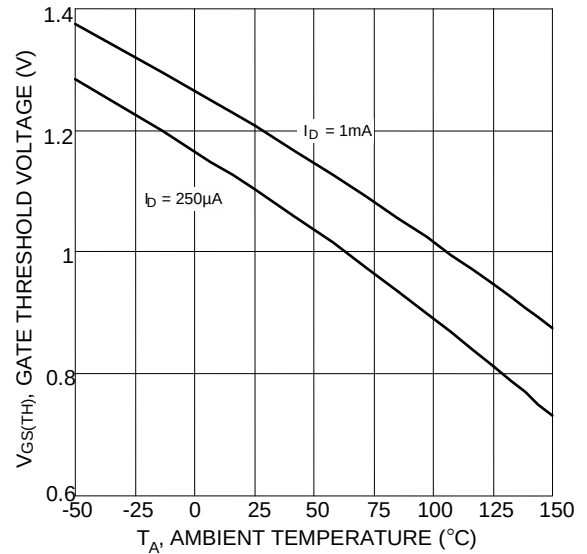


Figure 8 Gate Threshold Variation vs. Ambient Temperature

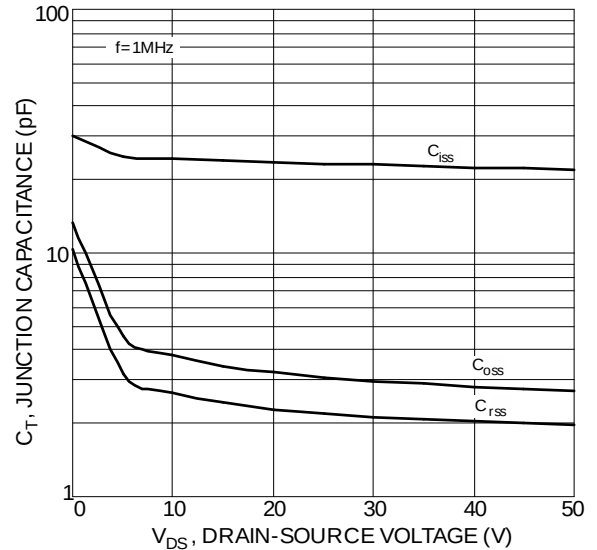


Figure 10 Typical Junction Capacitance

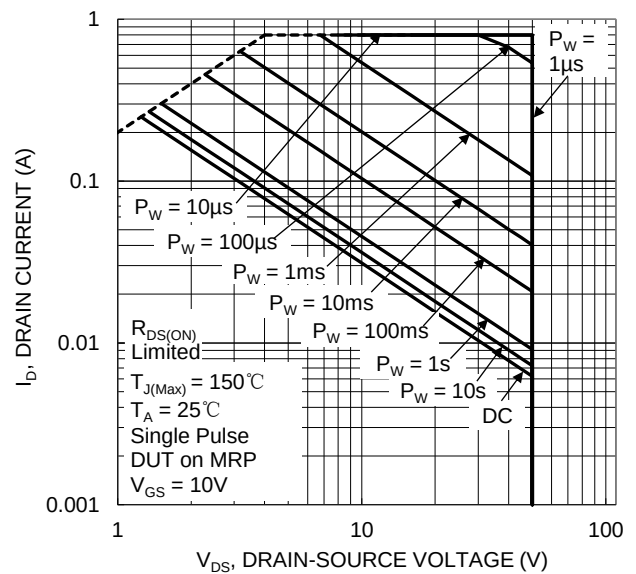


Figure 12 SOA, Safe Operation Area

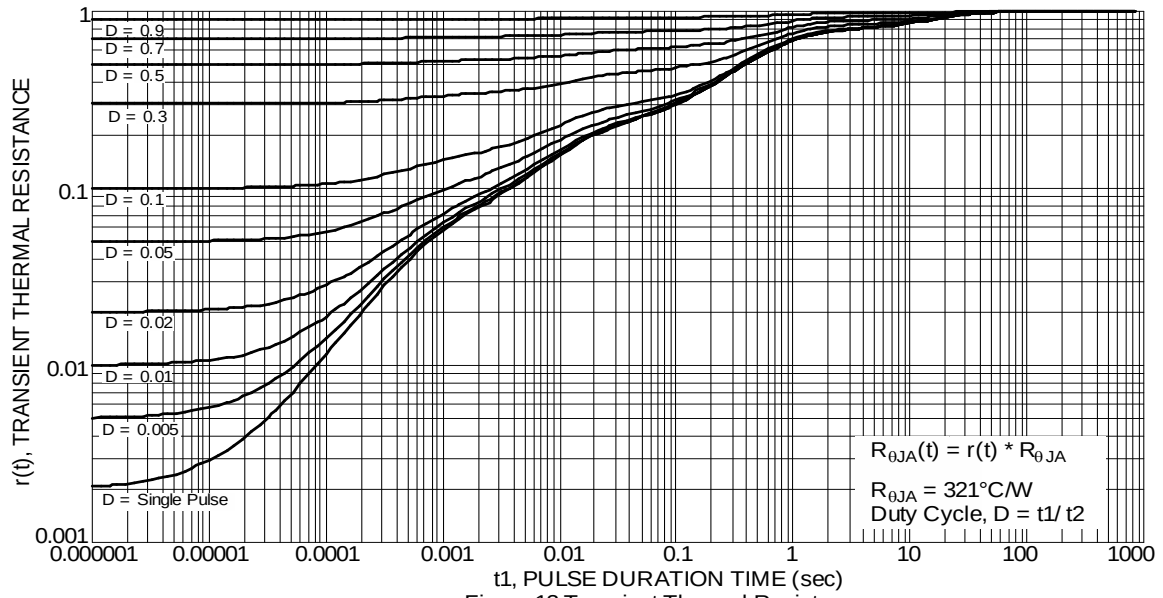
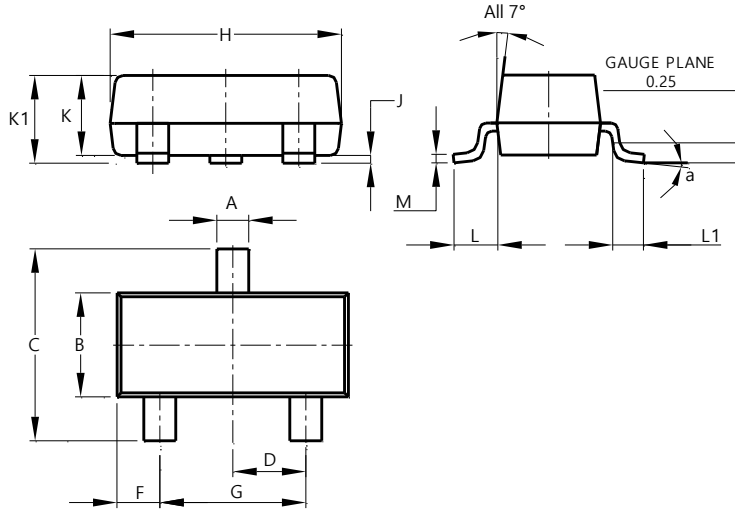


Figure 13 Transient Thermal Resistance

Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT23

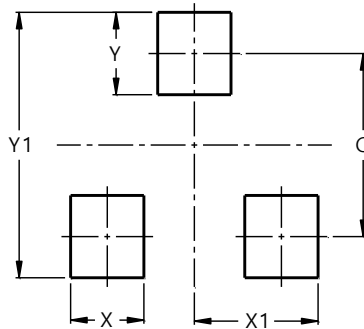


SOT23			
Dim	Min	Max	Typ
A	0.37	0.51	0.40
B	1.20	1.40	1.30
C	2.30	2.50	2.40
D	0.89	1.03	0.915
F	0.45	0.60	0.535
G	1.78	2.05	1.83
H	2.80	3.00	2.90
J	0.013	0.10	0.05
K	0.890	1.00	0.975
K1	0.903	1.10	1.025
L	0.45	0.61	0.55
L1	0.25	0.55	0.40
M	0.085	0.150	0.110
a	0°	8°	--
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT23



Dimensions	Value (in mm)
C	2.0
X	0.8
X1	1.35
Y	0.9
Y1	2.9

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